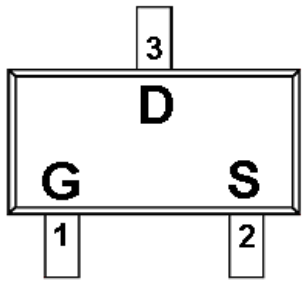
SPN2318
N-Channel Enhancement Mode MOSFET

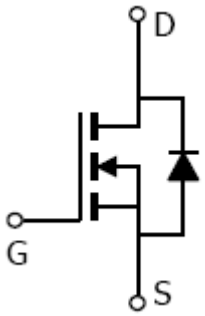
DESCRIPTION
The SPN2318 is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology.
This high density process is especially tailored to minimize on-state resistance.
These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits, and low in-line power loss are needed in a very small outline surface mount package.

APPLICATIONS
- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

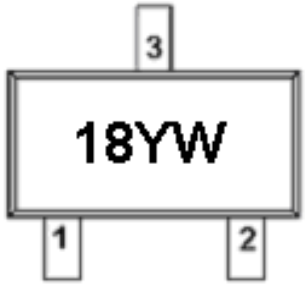
FEATURES
- 40V/3.9A,$R_{DS(ON)}$=56mΩ@V_{GS}=10V
- 40V/3.5A,$R_{DS(ON)}$=62mΩ@V_{GS}=4.5V
- 40V/2.0A,$R_{DS(ON)}$=95mΩ@V_{GS}=2.5V
- Super high density cell design for extremely low $R_{DS\ (ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-23-3L package design

PIN CONFIGURATION (SOT-23-3L)





PART MARKING



Y : Year Code
W : Week Code

SPN2318
N-Channel Enhancement Mode MOSFET

PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

ORDERING INFORMATION

Part Number	Package	Part Marking
SPN2318S23RGB	SOT-23-3L	18

※ Week Code : A ~ Z(1 ~ 26) ; a ~ z(27 ~ 52)
※ SPN2318S23RGB : Tape Reel ; Pb – Free ; Halogen -Free

ABSOULTE MAXIMUM RATINGS

(T_A=25℃ Unless otherwise noted)

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	40	V
Gate –Source Voltage		V_{GSS}	±12	V
Continuous Drain Current(T_J=150℃)	T_A=25℃	I_D	4.0	A
	T_A=70℃		3.0	
Pulsed Drain Current		I_{DM}	10	A
Continuous Source Current(Diode Conduction)		I_S	1.25	A
Power Dissipation	T_A=25℃	P_D	1.25	W
	T_A=70℃		0.8	
Operating Junction Temperature		T_J	150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	100	℃/W

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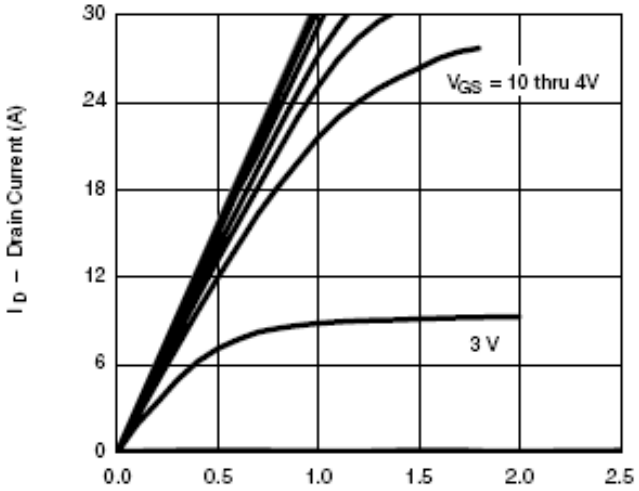
ELECTRICAL CHARACTERISTICS

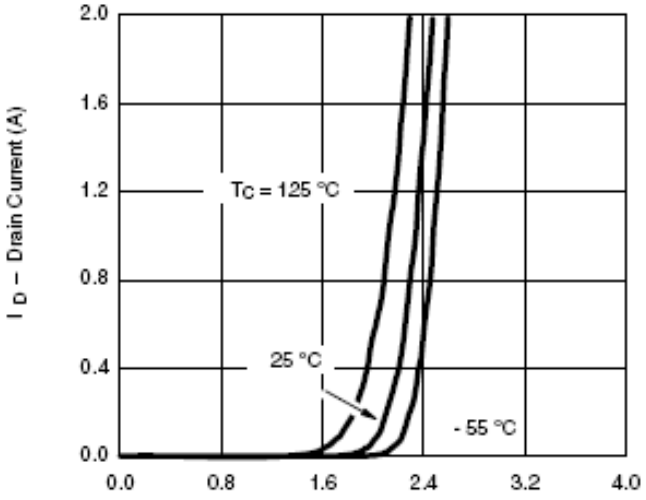
(T_A=25℃ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250uA	40			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	0.4		1.2	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±12V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=40V,V_{GS}=0V			1	uA
		V_{DS}=40V,V_{GS}=0V T_J=85℃			5	
On-State Drain Current	$I_{D(on)}$	V_{DS}= 5V,V_{GS} =4.5V	10			A
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}= 10V,I_D=3.9A		0.050	0.056	Ω
		V_{GS}=4.5V,I_D=3.5A		0.056	0.062	
		V_{GS}=2.5V,I_D=2.0A		0.088	0.095	
Forward Transconductance	gfs	V_{DS}=15V,I_D=6.2A		13		S
Diode Forward Voltage	V_{SD}	I_S=2.3A,V_{GS} =0V		0.8	1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=15V,V_{GS}=10V I_D= 2A		10	15	nC
Gate-Source Charge	Q_{gs}			1.6		
Gate-Drain Charge	Q_{gd}			2.0		
Input Capacitance	C_{iss}	V_{DS}=20V,V_{GS}=0V f=1MHz		500		pF
Output Capacitance	C_{oss}			80		
Reverse Transfer Capacitance	C_{rss}			45		
Turn-On Time	$t_{d(on)}$	V_{DD}=15V,R_L=15Ω I_D≡1.0A,V_{GEN}=10V R_G=6Ω		15	20	nS
	t_r			6	12	
Turn-Off Time	$t_{d(off)}$			10	20	
	t_f			40	80	

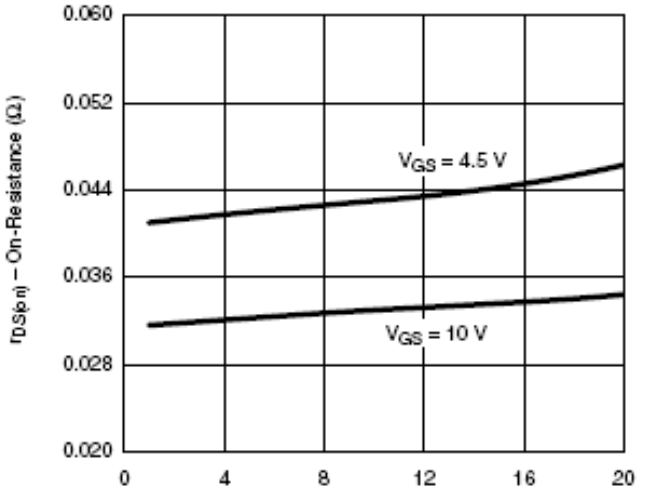
TYPICAL CHARACTERISTICS



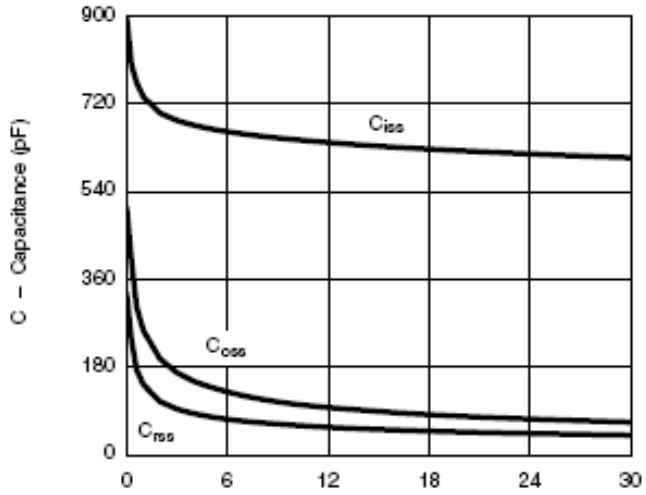
Output Characteristics



Transfer Characteristics

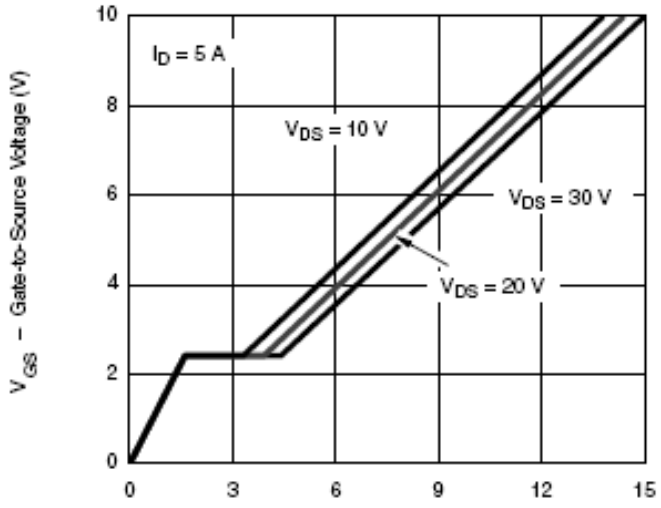


On-Resistance vs. Drain Current and Gate Voltage

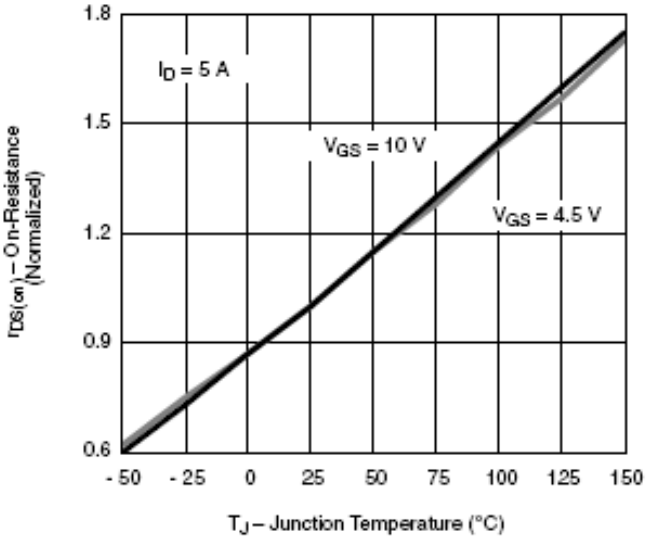


Capacitance

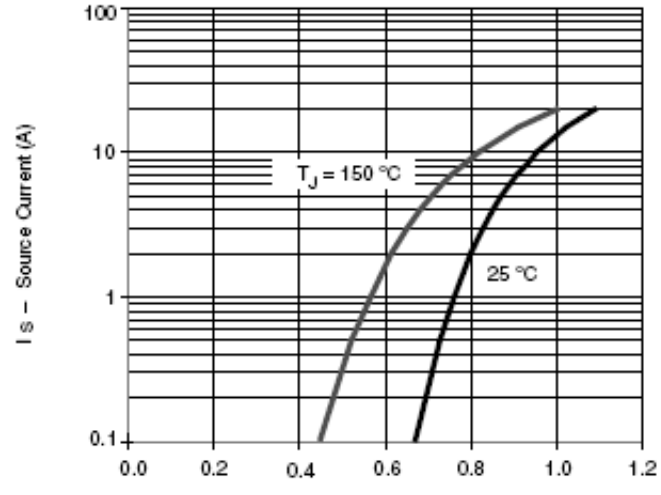
TYPICAL CHARACTERISTICS



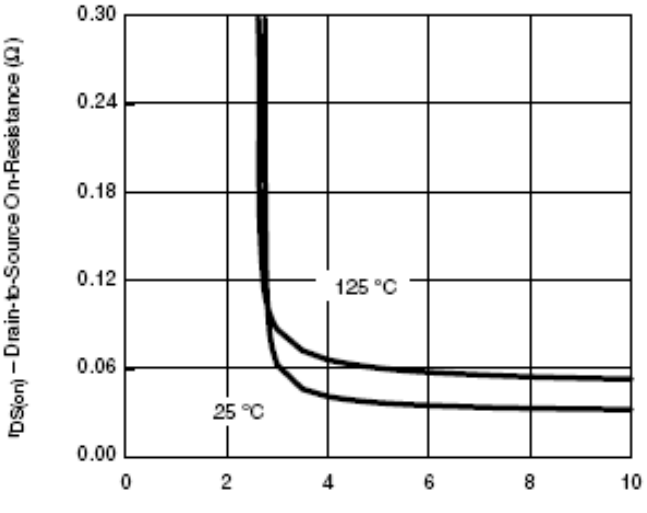
Gate Charge



On-Resistance vs. Junction Temperature

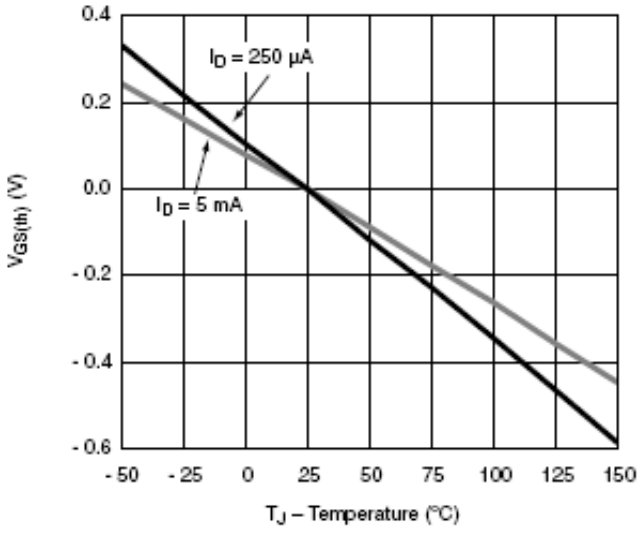


Source-Drain Diode Forward Voltage

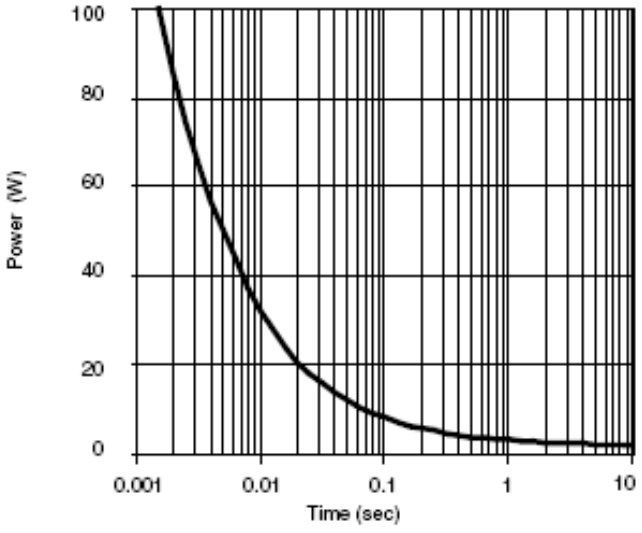


On-Resistance vs. Gate-to-Source Voltage

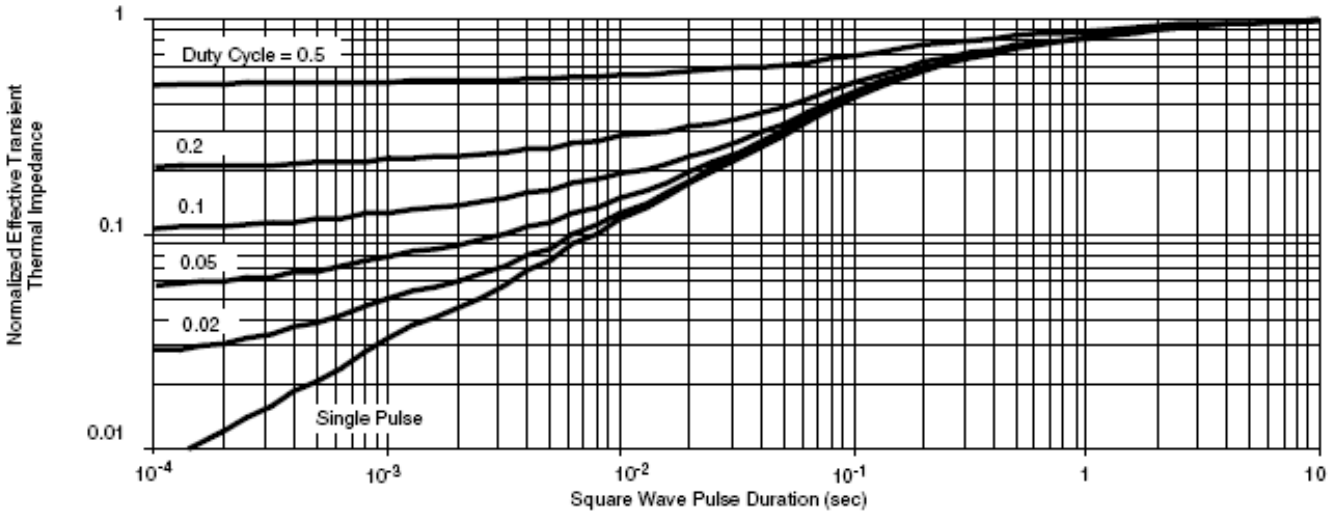
TYPICAL CHARACTERISTICS



Threshold Voltage



Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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